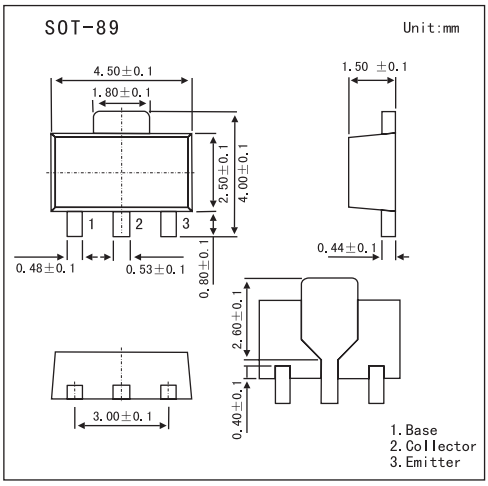
NPN Epitaxial Planar Silicon Transistor

2SC4520



■ Features

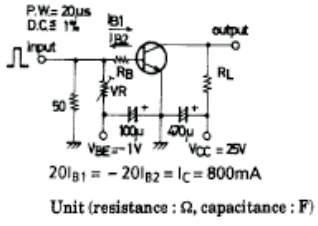
- Adoption of FBET, MBIT process.
- Large current capacity.
- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Small-sized package.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	45	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1.5	A
Collector current (pulse)	I_{CP}	3	A
Collector dissipation	P_C	1.3	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

2SC4520

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 45V, I_E=0			1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 3V, I_C=0			1	μA
DC current gain	h_{FE}	V_{CE} = 2V , I_C = 100mA	100		400	
Gain bandwidth product	f_T	V_{CE} = 2V , I_C = 100mA		300		MHz
Output capacitance	C_{ob}	V_{CB} = 10V , f = 1.0MHz		13		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 800 mA , I_B = 40mA		0.25	0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 800 mV , I_B = 40mA		0.9	1.3	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V
Turn-on time	t_{on}	 $20I_{B1} = -20I_{B2} = I_C = 800mA$ Unit (resistance : Ω, capacitance : F)		50	100	ns
Storage time	t_{stg}			150	270	ns
Fall time	t_f			180	350	ns

■ h_{FE} Classification

Marking	CK		
Rank	R	S	T
hFE	100～200	140～280	200～400